

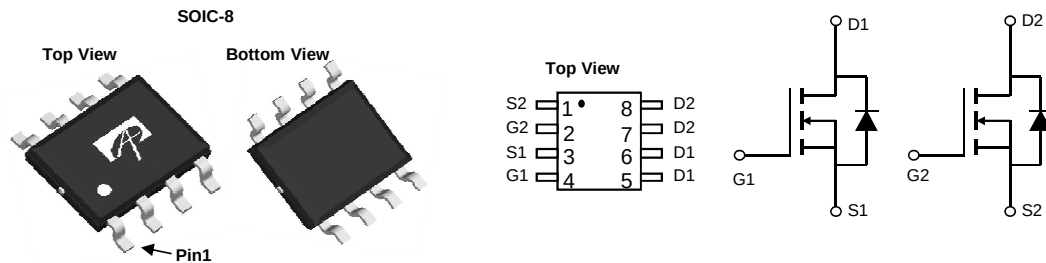
General Description

The AO4800B uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The two MOSFETs make a compact and efficient switch and synchronous rectifier combination for use in buck converters.

Product Summary

V_{DS}	30V
I_D (at $V_{GS}=10V$)	6.9A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 27m Ω
$R_{DS(ON)}$ (at $V_{GS} = 4.5V$)	< 32m Ω
$R_{DS(ON)}$ (at $V_{GS} = 2.5V$)	< 50m Ω

100% UIS Tested
 100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	6.9	A
		5.8	
Pulsed Drain Current ^C	I_{DM}	30	
Avalanche Current ^C	I_{AS}, I_{AR}	14	A
Avalanche energy $L=0.1\text{mH}$ ^C	E_{AS}, E_{AR}	10	mJ
Power Dissipation ^B	P_D	2	W
		1.3	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	48	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A,D}		74	90	$^\circ\text{C/W}$
Maximum Junction-to-Lead	$R_{\theta JL}$	32	40	$^\circ\text{C/W}$

Electrical Characteristics (T_j=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _j =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±12V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.7	1.1	1.5	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	30			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =6.9A T _j =125°C		17.8 28	27 40	mΩ
		V _{GS} =4.5V, I _D =6A		19	32	mΩ
		V _{GS} =2.5V, I _D =5A		24	50	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =5A		33		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current				2.5	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		630		pF
C _{oss}	Output Capacitance			75		pF
C _{rss}	Reverse Transfer Capacitance			50		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	1.5	3	4.5	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =15V, I _D =6.9A		6	7	nC
Q _{gs}	Gate Source Charge			1.3		nC
Q _{gd}	Gate Drain Charge			1.8		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =2.2Ω, R _{GEN} =3Ω		3		ns
t _r	Turn-On Rise Time			2.5		ns
t _{D(off)}	Turn-Off DelayTime			25		ns
t _f	Turn-Off Fall Time			4		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =6.9A, di/dt=100A/μs		8.5		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =6.9A, di/dt=100A/μs		2.6		nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using ≤ 10s junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

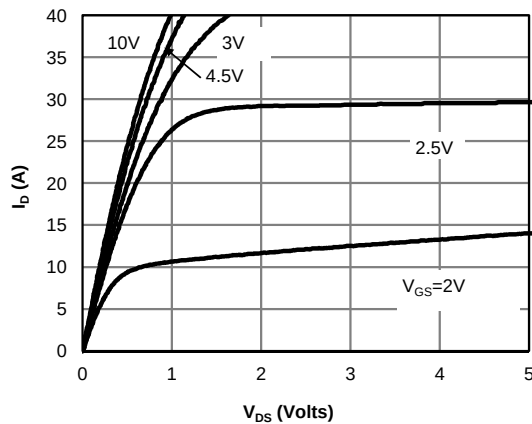


Fig 1: On-Region Characteristics (Note E)

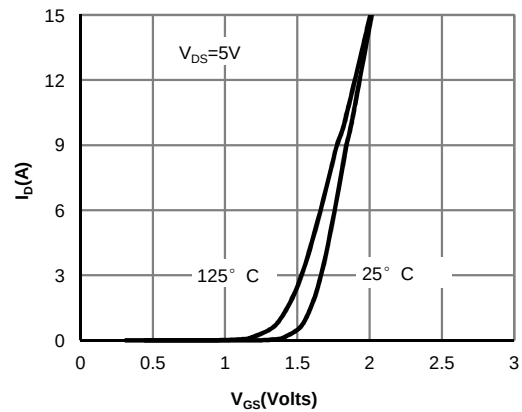


Figure 2: Transfer Characteristics (Note E)

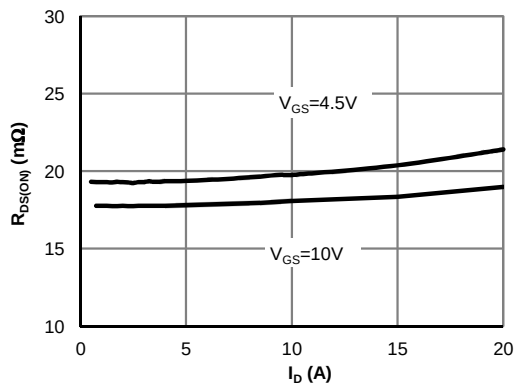


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

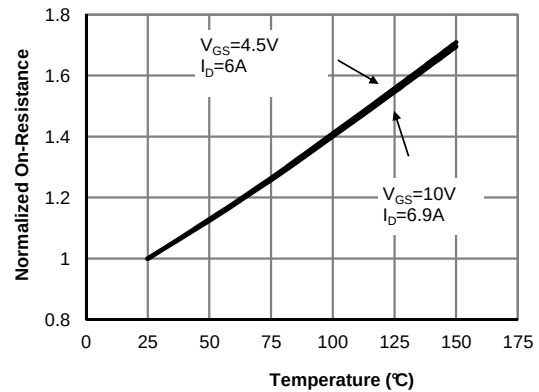


Figure 4: On-Resistance vs. Junction Temperature (Note E)

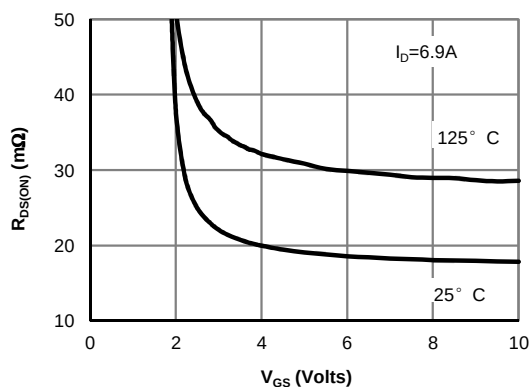


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

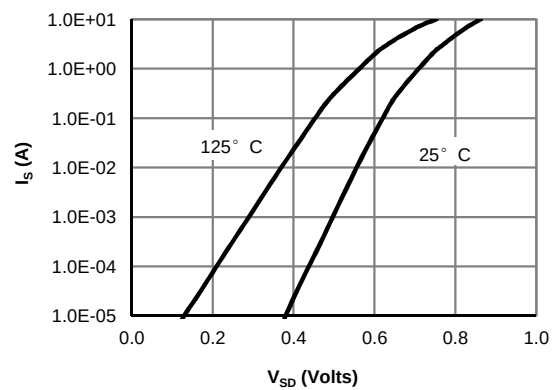


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

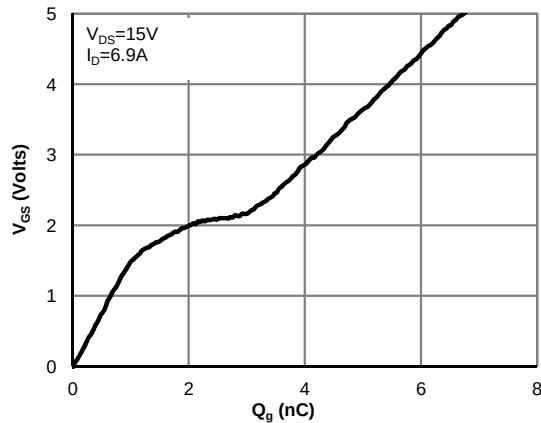


Figure 7: Gate-Charge Characteristics

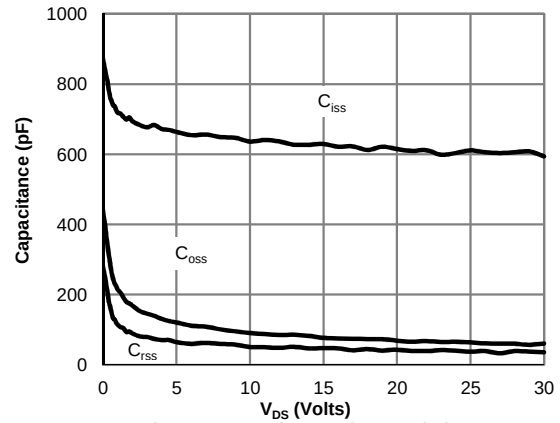


Figure 8: Capacitance Characteristics

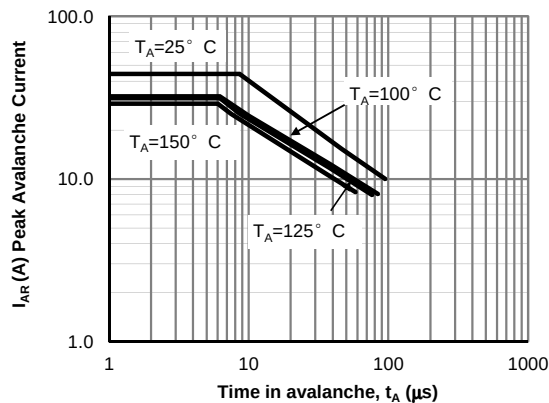


Figure 9: Single Pulse Avalanche capability (Note C)

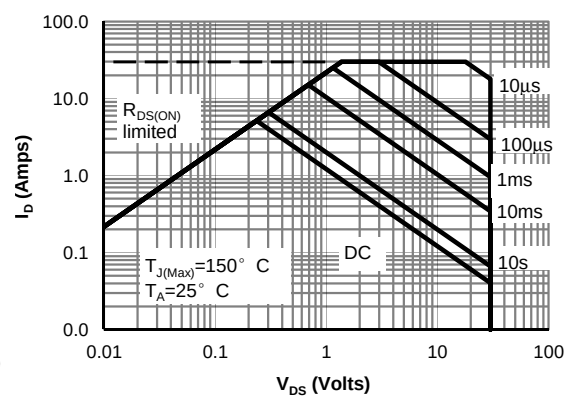


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

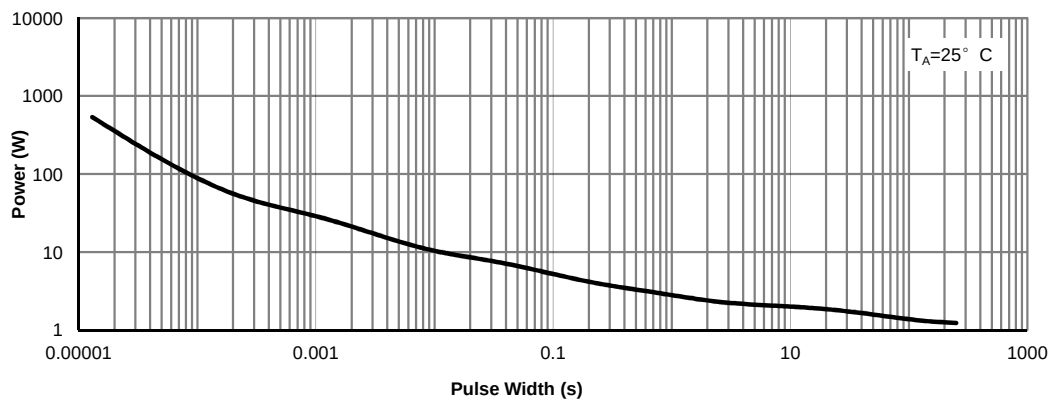


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

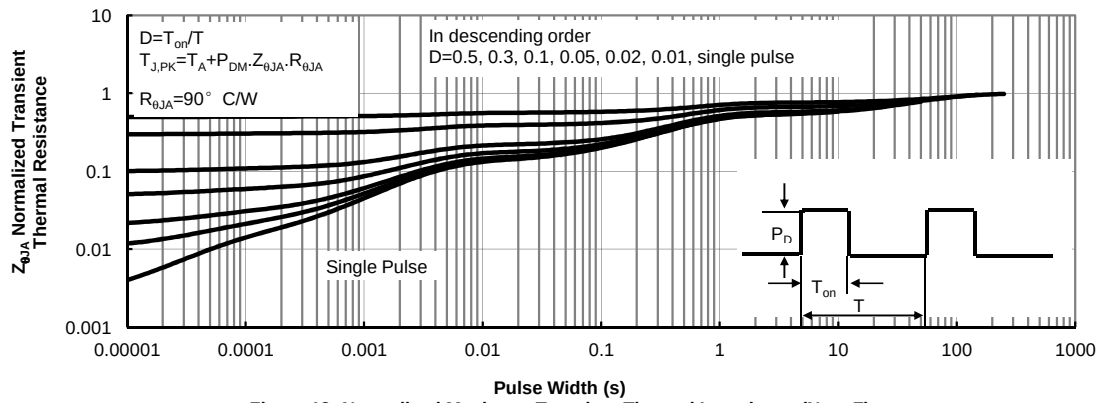
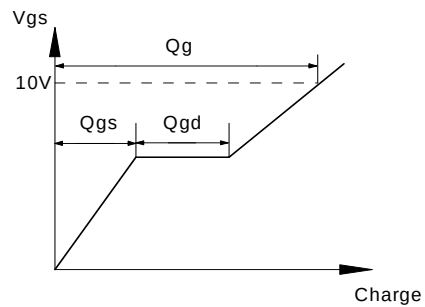
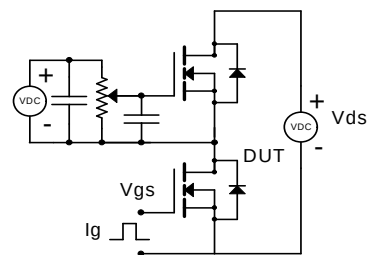
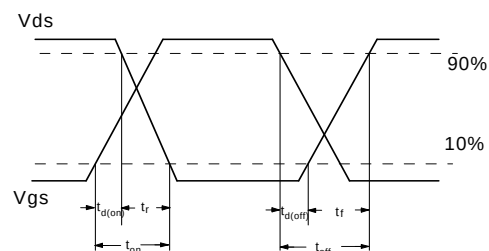
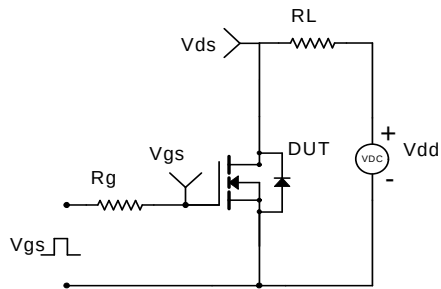


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

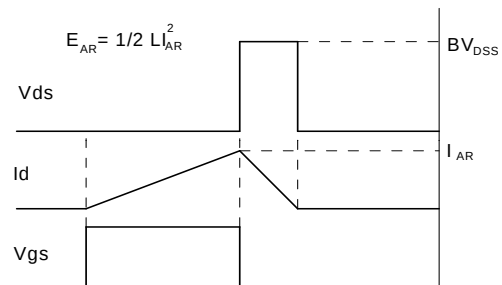
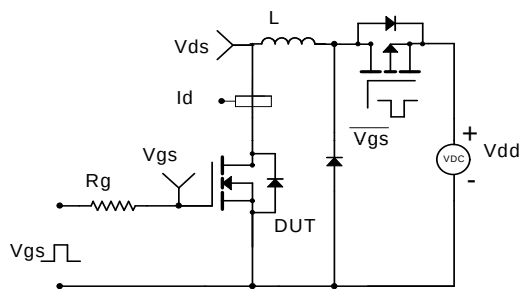
Gate Charge Test Circuit & Waveform



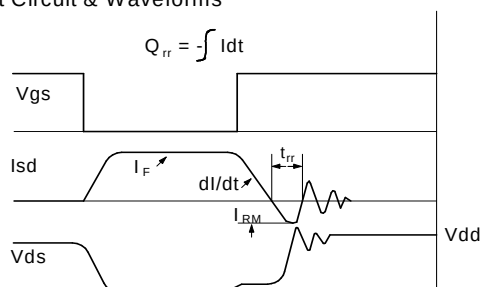
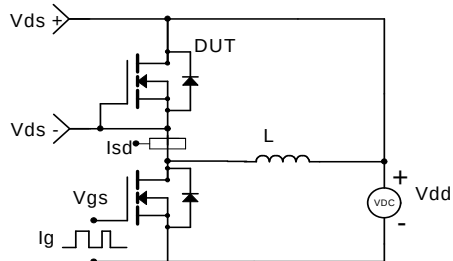
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



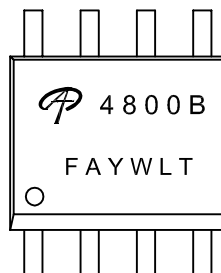
Diode Recovery Test Circuit & Waveforms





Document No.	PD-00655
Version	D
Title	AO4800B Marking Description

SO8 PACKAGE MARKING DESCRIPTION



Green product

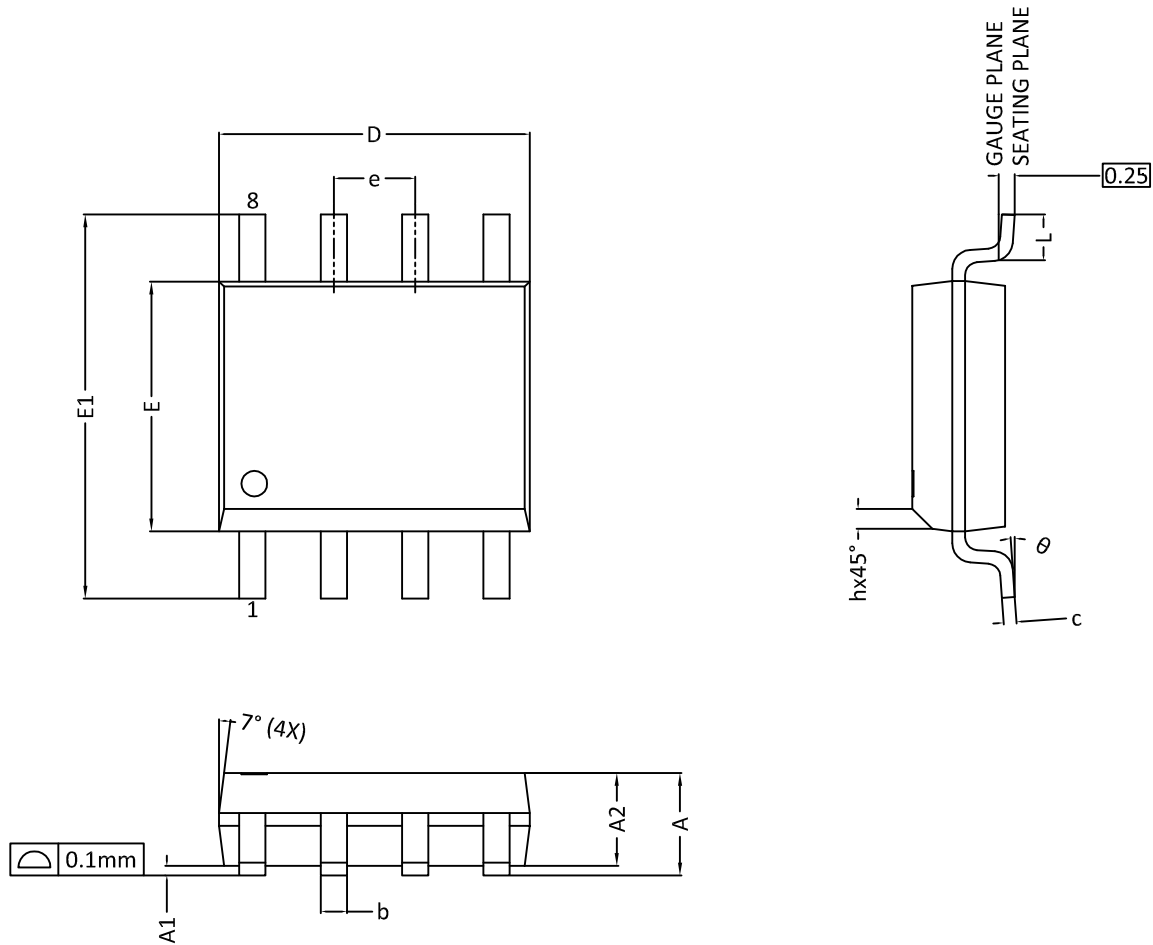
NOTE:

LOGO - AOS Logo
4800B - Part number code
F - Fab code
A - Assembly location code
Y - Year code
W - Week code
L&T - Assembly lot code

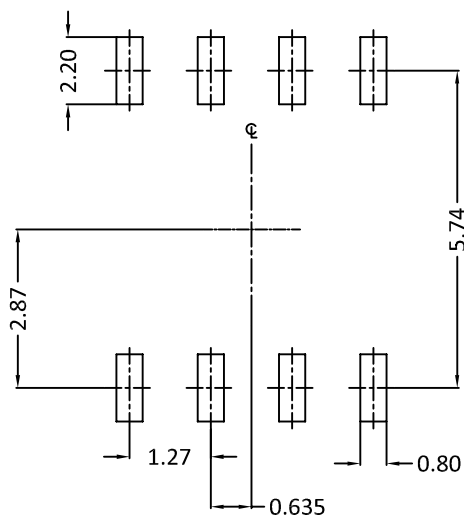
PART NO.	DESCRIPTION	CODE
AO4800B	Green product	4800B
AO4800BL	Green product	4800B



SO8(SOP-8L) PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



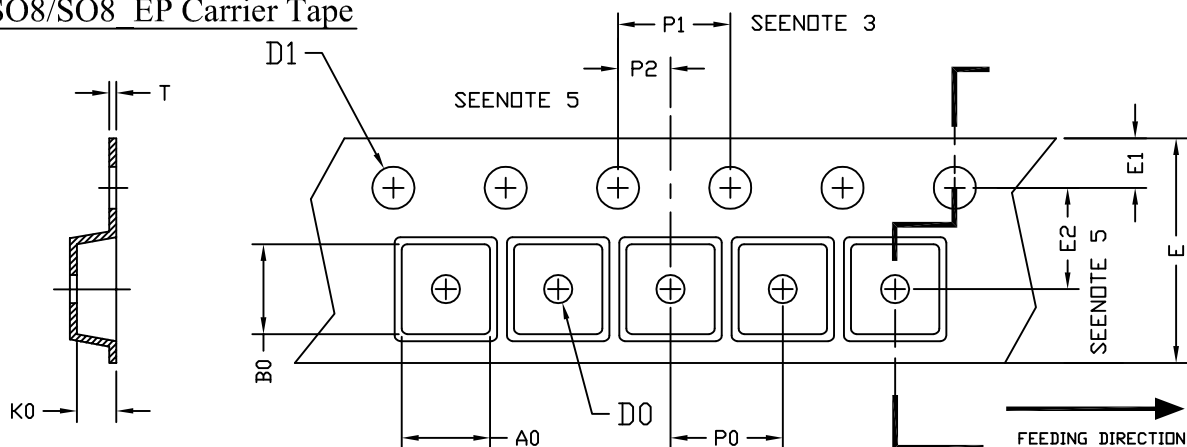
SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.35	1.65	1.75	0.053	0.065	0.069
A1	0.10	0.15	0.25	0.004	0.006	0.010
A2	1.25	1.50	1.65	0.049	0.059	0.065
b	0.31	0.41	0.51	0.012	0.016	0.020
c	0.17	0.20	0.25	0.007	0.008	0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
E	3.80	3.90	4.00	0.150	0.154	0.157
E1	5.80	6.00	6.20	0.228	0.236	0.244
e	1.27 BSC			0.050 BSC		
h	0.25	0.30	0.50	0.010	0.012	0.020
L	0.40	0.69	1.27	0.016	0.027	0.050
θ	0°	4°	8°	0°	4°	8°

UNIT: mm

NOTE

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONS ARE INCLUSIVE OF PLATING.
3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
4. DIMENSION L IS MEASURED IN GAUGE PLANE.
5. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

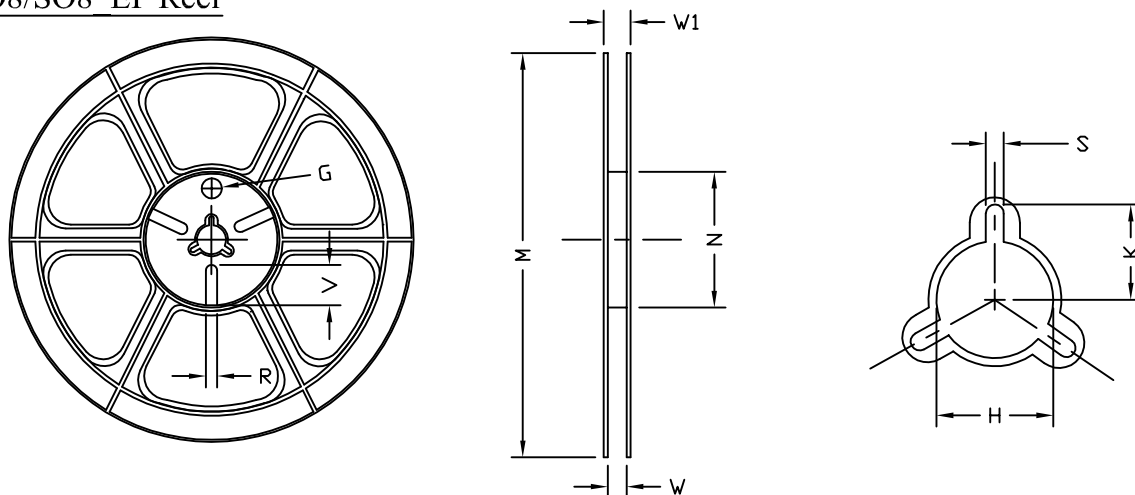
SO7/SO8/SO8 EP Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SO7/SO-8 (12 mm)	6.40 ±0.10	5.20 ±0.10	2.10 ±0.10	1.60 ±0.10	1.50 +0.10	12.00 ±0.30	1.75 ±0.10	5.50 ±0.05	8.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.25 ±0.05

SO7/SO8/SO8 EP Reel



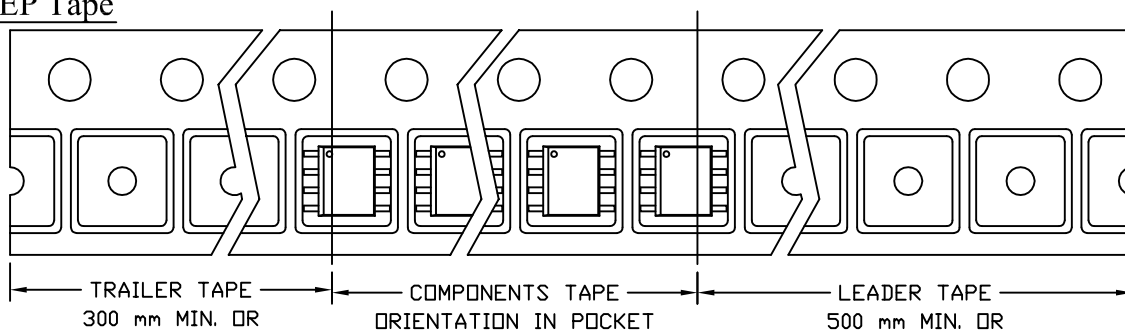
UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	Ø330	Ø330.00 ±0.50	Ø97.00 ±0.10	13.00 ±0.30	17.40 ±1.00	Ø13.00 +0.50 -0.20	10.60	2.00 ±0.50	---	---	---

SO7/SO8/SO8 EP Tape

Leader / Trailer
& Orientation

Unit Per Reel:
3000pcs





AOS Semiconductor

Product Reliability Report

AO4800B/AO4800BL, rev A

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

**495 Mercury Drive
Sunnyvale, CA 94085
U.S.**

Tel: (408) 830-9742

www.aosmd.com

Oct 15, 2007

This AOS product reliability report summarizes the qualification result for AO4800B. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO4800B passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

Table of Contents:

- I. Product Description
- II. Package and Die information
- III. Environmental Stress Test Summary and Result
- IV. Reliability Evaluation
- V. Quality Assurance Information

I. Product Description:

The AO4800B uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The two MOSFETs make a compact and efficient switch and synchronous rectifier combination for use in buck converters. Standard Product AO4800B is Pb-free (meets ROHS & Sony 259 specifications).

Absolute Maximum Ratings $T_A=25^{\circ}\text{C}$ unless otherwise noted				
Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current	$T_A=25^{\circ}\text{C}$	I_D	6.9	A
	$T_A=70^{\circ}\text{C}$		5.8	
Pulsed Drain Current		I_{DM}	40	
Power Dissipation	$T_A=25^{\circ}\text{C}$	P_D	1.9	W
	$T_A=70^{\circ}\text{C}$		1.2	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient	$T \leq 10\text{s}$	$R_{\theta JA}$	55	62.5	$^{\circ}\text{C/W}$
Maximum Junction-to-Ambient	Steady-State		90	110	$^{\circ}\text{C/W}$
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	40	48	$^{\circ}\text{C/W}$

II. Die / Package Information:

	AO4800B	AO4800BL (Green Compound)
Process	Standard sub-micron Low voltage N channel process	Standard sub-micron Low voltage N channel process
Package Type	8 leads SOIC	8 leads SOIC
Lead Frame	Copper with Ag spot	Copper with Ag spot
Die Attach	Ag epoxy	Ag epoxy
Bond wire	S: Cu 2mils; G: Au 1.3mils	S: Cu 2mils; G: Au 1.3mils
Mold Material	Epoxy resin with silica filler	Epoxy resin with silica filler
Filler % (Spherical/Flake)	90/10	100/0
Flammability Rating	UL-94 V-0	UL-94 V-0
Backside Metallization	Ti / Ni / Ag	Ti / Ni / Ag
Moisture Level	Up to Level 1 *	Up to Level 1 *

Note * based on info provided by assembler and mold compound supplier

III. Result of Reliability Stress for AO4800B (Standard) & AO4800BL (Green)

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures
Solder Reflow Precondition	Standard: 1hr PCT+3 cycle reflow@260°C Green: 168hr 85°C /85%RH +3 cycle reflow@260°C	0hr	Standard: 7 lots	770 pcs	0
HTGB	Temp = 150°C , Vgs=100% of Vgsmax	168 / 500 hrs 1000 hrs	1 lot (Note A*)	82 pcs 77+5 pcs / lot	0
HTRB	Temp = 150°C , Vds=80% of Vdsmax	168 / 500 hrs 1000 hrs	1 lot (Note A*)	82 pcs 77+5 pcs / lot	0
HAST	130 +/- 2°C , 85%RH, 33.3 psi, Vgs = 80% of Vgs max	100 hrs	Standard: 3 lots (Note B**)	165 pcs 50+5 pcs / lot	0
Pressure Pot	121°C , 29.7psi, 100%RH	96 hrs	Standard: 4 lots (Note B**)	220 pcs 50+5 pcs / lot	0
Temperature Cycle	-65°C to 150°C , air to air	250 / 500 cycles	Standard: 7 lots (Note B**)	385 pcs 50+5 pcs / lot	0

III. Result of Reliability Stress for AO4800B (Standard) & AO4800BL (Green)

Continues

DPA	Internal Vision Cross-section X-ray	NA	5 5 5	5 5 5	0
CSAM		NA	5	5	0
Bond Integrity	Room Temp 150°C bake 150°C bake	0hr 250hr 500hr	40 40 40	40 wires 40 wires 40 wires	0
Solderability	245°C	5 sec	15	15 leads	0
Die shear	150°C	0hr	10	10	0

Note A: The HTGB and HTRB reliability data presents total of available AO4800B and AO4800BL burn-in data up to the published date.

Note B: The pressure pot, temperature cycle and HAST reliability data for AO4800B and AO4800BL comes from the AOS generic package qualification data.

IV. Reliability Evaluation

FIT rate (per billion):128

MTTF = 891years

In general, 500 hrs of HTGB, 150 deg C accelerated stress testing is equivalent to 15 years of lifetime at 55 deg C operating conditions (by applying the Arrhenius equation with an activation energy of 0.7eV and 60% of upper confidence level on the failure rate calculation). AOS reliability group also routinely monitors the product reliability up to 1000 hr at and performs the necessary failure analysis on the units failed for reliability test(s).

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO4800B). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

$$\text{Failure Rate} = \text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)] = 1.83 \times 10^9 / [2 (164) (168) (258)] = 128$$

$$\text{MTTF} = 10^9 / \text{FIT} = 7.81 \times 10^6 \text{hrs} = 891 \text{years}$$

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor **[Af]** = $\text{Exp} [Ea / k (1/Tj u - 1/Tj s)]$

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

k = Boltzmann's constant, $8.617164 \times 10^{-5} \text{eV} / \text{K}$



V. Quality Assurance Information

Acceptable Quality Level for outgoing inspection: **0.1%** for electrical and visual.

Guaranteed Outgoing Defect Rate: **< 25 ppm**

Quality Sample Plan: conform to **Mil-Std-105D**